

# BC858CDXV6T1, BC858CDXV6T5

## Dual General Purpose Transistor

### PNP Dual

This transistor is designed for general purpose amplifier applications. It is housed in the SOT-563 which is designed for low power surface mount applications.

#### Features

- These are Pb-Free Devices

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	-30	V
Collector-Base Voltage	$V_{CBO}$	-30	V
Emitter-Base Voltage	$V_{EBO}$	-5.0	V
Collector Current - Continuous	$I_C$	-100	mAdc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

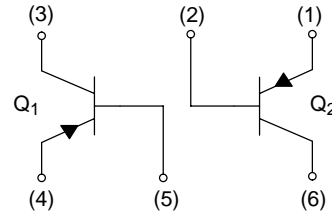
Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation, (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	357 2.9	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	350	$^\circ\text{C}/\text{W}$
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation, (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	500 4.0	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

1. FR-4 @ Minimum Pad



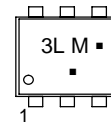
ON Semiconductor®

<http://onsemi.com>



SOT-563  
CASE 463A  
PLASTIC

#### MARKING DIAGRAMS



3L = Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping†
BC858CDXV6T1	SOT-563	4000/Tape & Reel
BC858CDXV6T1G	SOT-563 (Pb-Free)	4000/Tape & Reel
BC858CDXV6T5	SOT-563	8000/Tape & Reel
BC858CDXV6T5G	SOT-563 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# BC858CDXV6T1, BC858CDXV6T5

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Breakdown Voltage ( $I_C = -10\text{ mA}$ )	$V_{(BR)CEO}$	-30	-	-	V
Collector–Emitter Breakdown Voltage ( $I_C = -10\text{ }\mu\text{A}$ , $V_{EB} = 0$ )	$V_{(BR)CES}$	-30	-	-	V
Collector–Base Breakdown Voltage ( $I_C = -10\text{ }\mu\text{A}$ )	$V_{(BR)CBO}$	-30	-	-	V
Emitter–Base Breakdown Voltage ( $I_E = -1.0\text{ }\mu\text{A}$ )	$V_{(BR)EBO}$	-5.0	-	-	V
Collector Cutoff Current ( $V_{CB} = -30\text{ V}$ ) ( $V_{CB} = -30\text{ V}$ , $T_A = 150^\circ\text{C}$ )	$I_{CBO}$	-	-	-15 -4.0	nA $\mu\text{A}$
<b>ON CHARACTERISTICS</b>					
DC Current Gain ( $I_C = -10\text{ }\mu\text{A}$ , $V_{CE} = -5.0\text{ V}$ ) ( $I_C = -2.0\text{ mA}$ , $V_{CE} = -5.0\text{ V}$ )	$h_{FE}$	- 420	270 520	- 800	-
Collector–Emitter Saturation Voltage ( $I_C = -10\text{ mA}$ , $I_B = -0.5\text{ mA}$ ) ( $I_C = -100\text{ mA}$ , $I_B = -5.0\text{ mA}$ )	$V_{CE(sat)}$	- -	- -	-0.3 -0.65	V
Base–Emitter Saturation Voltage ( $I_C = -10\text{ mA}$ , $I_B = -0.5\text{ mA}$ ) ( $I_C = -100\text{ mA}$ , $I_B = -5.0\text{ mA}$ )	$V_{BE(sat)}$	- -	-0.7 -0.9	- -	V
Base–Emitter On Voltage ( $I_C = -2.0\text{ mA}$ , $V_{CE} = -5.0\text{ V}$ ) ( $I_C = -10\text{ mA}$ , $V_{CE} = -5.0\text{ V}$ )	$V_{BE(on)}$	-0.6 -	- -	-0.75 -0.82	V
<b>SMALL–SIGNAL CHARACTERISTICS</b>					
Current–Gain–Bandwidth Product ( $I_C = -10\text{ mA}$ , $V_{CE} = -5.0\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	100	-	-	MHz
Output Capacitance ( $V_{CB} = -10\text{ V}$ , $f = 1.0\text{ MHz}$ )	$C_{ob}$	-	-	4.5	pF
Noise Figure ( $I_C = -0.2\text{ mA}$ , $V_{CE} = -5.0\text{ Vdc}$ , $R_S = 2.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ , $BW = 200\text{ Hz}$ )	NF	-	-	10	dB

TYPICAL CHARACTERISTICS

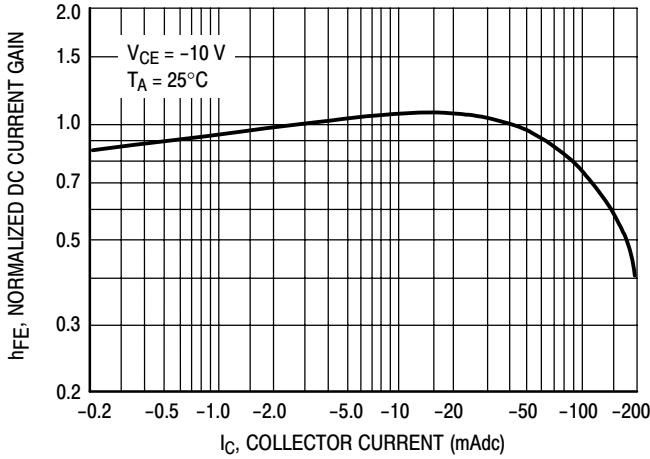


Figure 1. Normalized DC Current Gain

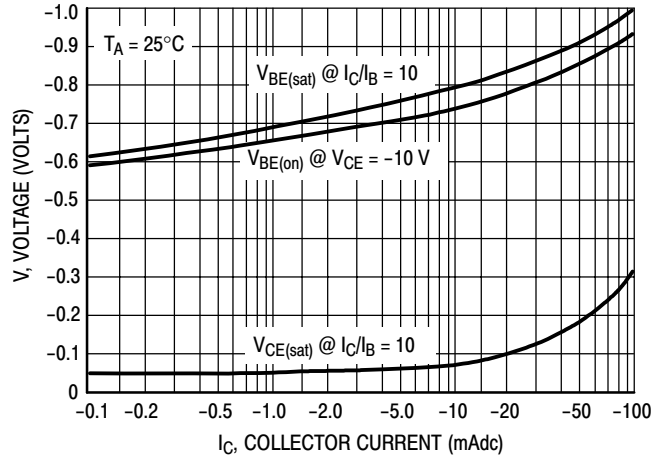


Figure 2. "Saturation" and "On" Voltages

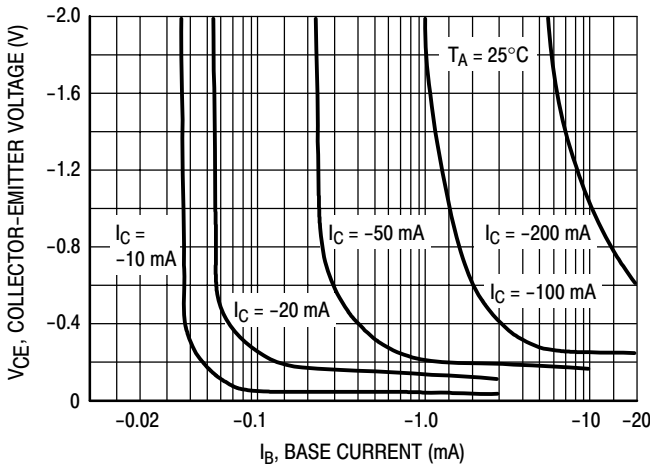


Figure 3. Collector Saturation Region

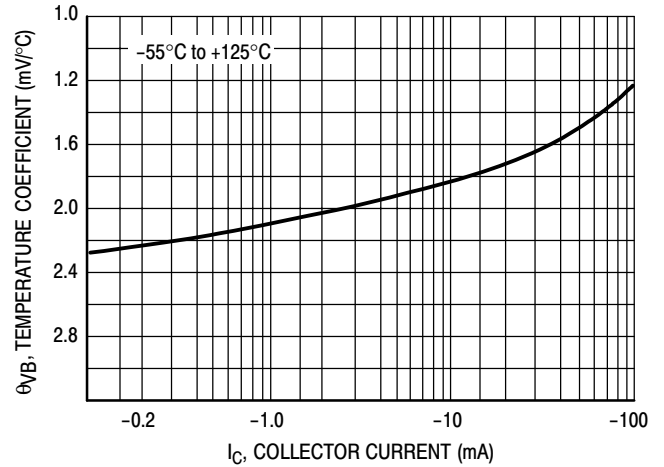


Figure 4. Base-Emitter Temperature Coefficient

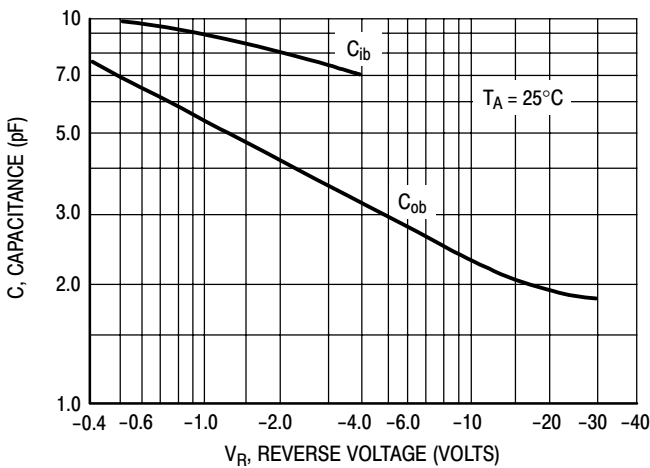


Figure 5. Capacitances

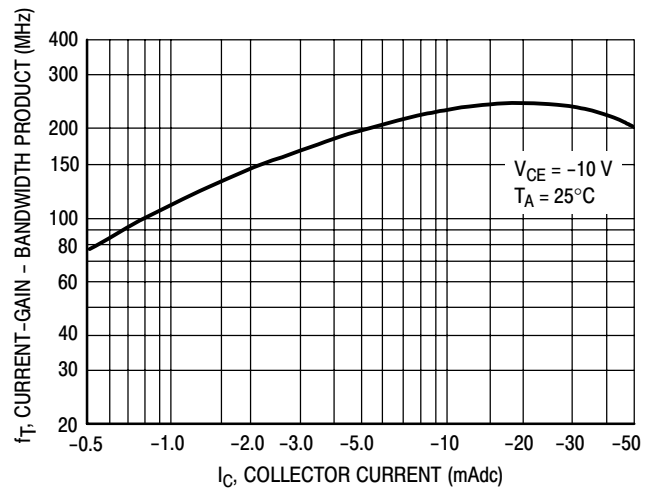
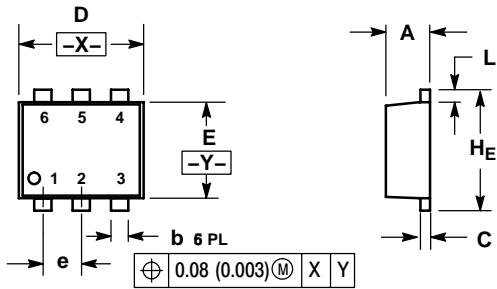


Figure 6. Current-Gain - Bandwidth Product

# BC858CDXV6T1, BC858CDXV6T5

## PACKAGE DIMENSIONS

SOT-563, 6 LEAD  
CASE 463A-01  
ISSUE F



### NOTES:

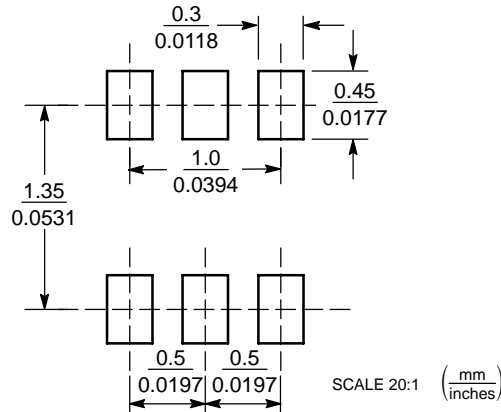
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
C	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
E	1.10	1.20	1.30	0.043	0.047	0.051
e	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H <sub>E</sub>	1.50	1.60	1.70	0.059	0.062	0.066

### STYLE 1:

- PIN 1. EMITTER 1
- BASE 1
- COLLECTOR 2
- EMITTER 2
- BASE 2
- COLLECTOR 1

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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